

Graphite-Si-SiC ceramics produced by microwave assisted reactive melt infiltration

Original

Graphite-Si-SiC ceramics produced by microwave assisted reactive melt infiltration / Padovano, E.; Giorcelli, M.; Bianchi, G.; Biamino, S.; Rovere, M.; Tagliaferro, A.; Ortona, A.. - In: JOURNAL OF THE EUROPEAN CERAMIC SOCIETY. - ISSN 0955-2219. - ELETTRONICO. - 39:7(2019), pp. 2232-2243. [10.1016/j.jeurceramsoc.2019.01.057]

Availability:

This version is available at: 11583/2743641 since: 2020-01-08T10:34:21Z

Publisher:

Elsevier Ltd

Published

DOI:10.1016/j.jeurceramsoc.2019.01.057

Terms of use:

This article is made available under terms and conditions as specified in the corresponding bibliographic description in the repository

Publisher copyright

(Article begins on next page)

Graphite-Si-SiC ceramics produced by microwave assisted reactive melt infiltration.

Elisa Padovano^{1*}, Mauro Giorcelli¹, Giovanni Bianchi², Sara Biamino¹, Massimo Rovere¹,
Alberto Tagliaferro^{1,3} and Alberto Ortona²

¹ Politecnico di Torino, Department of Applied Science and Technology, Corso Duca degli Abruzzi 24, 10129, Torino, Italy

² MEMTI-SUPSI, Strada Cantonale, CH-6928, Manno, Switzerland

³ Faculty of Science, University of Ontario Institute of Technology, Oshawa (ON), Canada

*Corresponding author: elisa.padovano@polito.it

Abstract

A novel microstructure of graphite-Si-SiC ceramics was successfully prepared by liquid silicon infiltration of graphite-based preforms; instead of using conventional methods, the reactive infiltration process was assisted by microwaves. The effects of microwave power variation on the microstructure and the mechanical properties of infiltrated materials were studied. X-ray diffraction and Raman investigations showed the presence of both unreacted graphite and Si in addition to SiC formed at their interface. The graphitic and silicon phases were separated by a SiC network, which results more homogeneous as microwave power was increased. The amount of SiC was found to be higher in function of the growing power level; a higher conversion of graphite into SiC yielded a more dense material. The bending strength measurements confirm this, showing higher values for the samples processed using a power level of 75% of the full power compared to those obtained with 30% and 60%.

Keywords

Reactive melt infiltration; Microwave; Graphite-based preforms; SiC; Raman spectroscopy

1. Introduction

Reactive melt infiltration (RMI) through a porous matrix is an alternative way to produce intermetallic, ceramic, and composite materials [1–4]. In comparison to other composite processing methods, RMI provides significant advantages such as short processing times and much lower operating temperatures with respect to the melting temperatures of produced materials. Nelson et al.[5] reported in fact that chemical vapour infiltration requires days or weeks to complete the conversion process, while RMI requires only minutes or hours to obtain

1 the final product from chemical reaction between the infiltrant and the preform. Margiotta et al.
2 [6] obtained dense SiC carrying out the liquid silicon infiltration of carbon preforms at 1800 °C
3 for 120 minutes; the temperature resulted much lower compared to both the melting point of
4 SiC (2730 °C) and the temperature generally required for SiC sintering. Moreover, the
5 materials produced by RMI show thermal properties comparable to those obtained by standard
6 processes. Wang et al.[7] prepared ZrB₂-SiC protective lamina to be used as coating on
7 carbon/carbon composites combining pressing and Reactive Silicon Infiltration (RSI). It
8 successfully avoids the oxygen penetration in the inner part of material thanks to the formation
9 of a surface oxide layer. The composition of it is similar to that observed for ZrB₂-SiC coating
10 processed by CVD [8]. The processing of ZrB₂-SiC coating by RSI represents a promising
11 alternative to generally used CVD films, which show similar ablation resistance, but require
12 long and high-cost processing methods. Moreover, Bianchi et al.[9] reported that the RSI
13 process yields Si-SiC foam bodies showing high thermal shock resistance, comparable to that
14 of similar foam produced by more conventional sponge replica techniques [10]. The economic
15 advantages in term of energy and time saving make the RMI process attractive for many
16 industrial applications such as aerospace, energy, automotive, biomedical and electronics
17 [9,11–13].

18 Si-SiC ceramics obtained by reactive infiltration of liquid silicon into carbonaceous preforms
19 have been widely investigated since the 70s [14]. The process is based on the exothermic
20 chemical reaction between a porous carbon preform and molten silicon. It shows some
21 advantages with respect to the more traditional processing methods for obtaining silicon
22 carbide: RMI does not require the use of any sintering aids, which are instead necessary by
23 using hot pressing and pressureless sintering [15,16].

24 RMI process is organized in three steps: (i) the manufacture of carbon/phenolic green bodies
25 followed by pyrolysis, (ii) infiltration of the bodies by molten silicon and (iii) the exothermic
26 chemical reaction between the liquid silicon and the solid carbon, which leads the formation of
27 a SiC matrix:



29 The manufacture of the preforms is the first key factor that has a great influence on the
30 properties of the final ceramic. The various carbon sources and the effects of their morphology,
31 micrometer-scale porosity and chemical reactivity on the process have been widely investigated
32 in the literature, as detailed [below](#).

1 According to Margiotta et al. [6], when the starting material is in powder form, the chemical
2 reactivity of solid carbon with molten silicon is strongly dependent on both the atomic ordering
3 and the porosity at atomic-scale level. In fact, a decrease of carbon atomic ordering and a
4 consequent increase of porosity at atomic level should promote the development of new “active
5 sites” favouring the reaction of carbon with molten Si.

6 Wang et al. [18] prepared glassy carbon preforms starting from a mixture of furfuryl resin and
7 alcohol, diethyleneglycol, triethyleneglycol, water and paratoluene sulfonic acid. These
8 components were then subjected to polymerization and pyrolysis at 700 °C. The use of glassy
9 carbon allows control of the size and the distribution of the pores in order to maximize the
10 infiltration process; on the other hand, with its relative high density, glassy carbon shows low
11 reactivity toward liquid silicon and therefore it cannot be considered an ideal substrate for the
12 liquid infiltration process [6]. The reaction between liquid silicon and glassy carbon leads to the
13 nucleation of SiC crystals and the formation of a thin layer at their interface; it acts as a
14 diffusion barrier preventing further reaction. The formation of silicon carbide may then proceed
15 through slow a diffusion process or it can even be interrupted [19].

16 Many studies are based on the use of cellulosic precursors, [6,20,21] which show a higher
17 chemical reactivity with silicon compared to that observed for glassy carbon; for these starting
18 polymeric materials the conversion of carbon in order to obtain silicon carbide is generally
19 fully successful. The main limit is linked to the difficulty in controlling the preform structure
20 with pores and capillary channels of the size required for the infiltration process. In this case
21 the dissolution of carbon into molten silicon is faster and therefore favoured with respect to the
22 nucleation of SiC.

23 Graphite is a very common and cheap carbon source showing high thermal conductivity, good
24 machinability and a thermal expansion coefficient close to that of silicon [22]. White et al. [22]
25 reported that open porosity, surface roughness and Si/C contact time are the main parameters
26 influencing the reactive wetting of liquid silicon to the graphite substrates. The use of graphite
27 in the RMI process may be limited by the formation of cracks during the infiltration process
28 caused by the development of internal stresses [22,23]. On the base of molar volume of the
29 species involved, ($V_{\text{graphite}}= 5.5 \text{ cm}^3/\text{mol}$, $V_{\text{Si}}= 11.6 \text{ cm}^3/\text{mol}$ and $V_{\text{SiC}}= 12.5 \text{ cm}^3/\text{mol}$ [23]) it is
30 clear that the reaction between silicon and graphite leading to the formation of SiC involves a
31 volume increase, which may induce the formation of cracks. Israel et al. [23] reported the
32 fracture of some infiltrated samples produced by using graphite-based preforms. The study

1 shows the capillary interaction between the molten silicon and the graphite during RMI process
2 by varying the porosity and the size of pores. Samples cracked when a graphite with a mean
3 pore diameter around 13 μm was used; this behaviour was not observed using others graphitic
4 starting materials with pores under 1 μm . White et al. [22] investigated the interaction of
5 molten silicon with different grades of graphite, which were used as starting materials for the
6 production of preforms. It was reported that the use of extruded graphite with high open
7 porosity, leads to the development of internal stresses during the infiltration process, which
8 causes the fracture of graphitic substrate. This confirms that the properties of starting graphite
9 strongly influence the success of RMI process.

10 This paper provides a detailed microstructural, Raman and crystallographic characterization of
11 graphite-Si-SiC materials produced by microwave (MW) assisted RMI. The starting carbon
12 preforms were obtained by grinding up large plates of graphite to decrease the particle size to
13 micrometric scale. The mechanical process of grain size reduction introduced many defects in
14 the structure of graphite and increases its chemical reactivity making the infiltration process
15 complex.

16 The successful processing of graphite-Si-SiC composites was first realized by Cornolti et al.
17 [24] and it was linked to a careful investigation and optimization of the infiltration process,
18 which involved the use of microwaves.

19 Unlike from conventional heating where the energy is transferred mainly through the surface of
20 the samples, the microwave radiation provides fast volumetric heating of the irradiated
21 component resulting in more efficient heat generation and transfer; a reduction in terms of total
22 energy consumption and processing time with respect to the standard methods were achieved
23 [25]. Danko et al. [26] processed silicon carbide and silicon oxycarbide ceramics by pyrolysis
24 of preceramic polymers using standard and microwaves heating systems. The properties of
25 materials in term of thermal stability and formed crystalline phases resulted comparable (larger
26 β -SiC crystallite size was observed for conventional-oven-heated samples). Moreover Breval et
27 al.[27] compared the properties of WC samples containing 6 % and 12 % of Co sintered in
28 conventional and microwave furnaces. The microwave sintered samples showed a higher
29 values of hardness (from 1 to 5 GPa) than conventionally sintered samples, in addition to better
30 resistance towards both corrosion and erosion.

31 Microwave-assisted processes allow to obtaining promising results in term of both
32 development of materials with improved properties and new processing routes at laboratory

1 scale. However, there is a growing interest in transfer these advantages to an industrial scale.
2 According to Banos et al. [28] the main limits that need to be overcome are mainly linked to
3 the knowledge of the phenomena associated with the MW processes. The interaction between
4 the microwaves and the matter is a very complex item which is nowadays a matter of study,
5 especially when the process involves high temperatures. Another barrier is the limited
6 knowledge of the heating mechanisms when materials are subjected to high frequency fields. In
7 particular, the effects of electromagnetic fields on the materials' microstructure are still little
8 known [M-M interaction]. In this context the investigation on the dielectric properties of
9 materials is required in order to better design the MW-assisted process.

10 Different studies [29–32] investigated the materials' dielectric properties such as the dielectric
11 constant (or real permittivity, ϵ') and the dielectric loss factor (or imaginary permittivity, ϵ'')
12 and their variation as function of the temperature. This paper investigated MW-assisted process
13 involving graphite-based preform and silicon, which are then converted into SiC. Both the
14 starting materials show high microwave absorption properties: carbon materials are generally
15 considered good absorbent of microwaves because of they can be easily heated
16 by microwave radiation. Graphite is, for example, considered an efficient sensitizer: it converts
17 radiation energy into thermal energy, which is then transmitted to supported chemical
18 compounds favouring reactions which require high temperatures or which involve chemical
19 compounds showing a low dielectric loss factor [33]. Moreover silicon absorbs very well the
20 MW radiation at the frequency involved in the RMI process under investigation, as confirmed
21 by Cornolti et al.[24]. The European Project HELM [34], which investigates advanced
22 processing methods involving the use of microwaves and radiofrequencies for the processing
23 of ceramic matrix composites, determined the dielectric properties of beta-SiC prepared by
24 using graphite powder as carbon precursor and silicon. It was found that SiC shows a moderate
25 value of ϵ' in addition to a high value of ϵ'' . This combination of dielectric properties confirm
26 the optimum interaction of SiC with microwaves.

27 The conversion of graphite-based preforms into SiC can be controlled by varying the
28 microwave power; this paper investigates the effects of increasing microwave power on the
29 microstructure and properties of graphite-Si-SiC materials.

30

31 **2. Materials and methods**

32 **2.1 Preform preparation**

1 The materials of the preforms were graphite (TIMREX KS 5-75, IMERYS, Bodio,
2 Switzerland) and a phenolic novolac powder (BAKELITE PF GA T 10/R, Momentive
3 Speciality Chemicals, Germany). The properties of the KS 5-75 graphite powder are: ash
4 content 0.07 %, crystallite height $L_c > 10$ nm, bulk density = 0.24 g/cm^3 , particle size
5 distribution $d_{50} = 23.1 \text{ }\mu\text{m}$, $d_{90} = 55.8 \text{ }\mu\text{m}$.

6 The phenolic novolac powder employed was received in form of micro granules ($d_{50} = 64 \text{ }\mu\text{m}$
7 diameter). Graphite and the phenolic powder were dry mixed with a rotative mechanical mixer
8 (EIRICH, Walldürner, Germany) for 2 hours. 20 g of compound were uniaxially cold-pressed
9 (Ceramic Instruments, Sassuolo, Italy) at a pressure of 23 MPa for 30 seconds to obtain discs of
10 50 mm in diameter and 5 mm in thickness. Cold pressing was chosen to achieve a reasonable
11 porosity of the preforms after pyrolysis [35] for the following RMI stage.

12 The disks were pyrolysed in flowing Ar (300 sl/min) in an electric furnace (KEOS,
13 Concorezzo, Italy) with the following heating cycle: 21-500°C in 12 h (heating rate of 40 °C/h),
14 500-960 °C in 9 h (heating rate of 50°C), 1 h dwell at 960 °C and natural cooling. The pyrolysis
15 converted the phenolic compound into volatile monomers, hydrogen and glassy carbon.

16 Table 1 shows the different weight percentages of material before and after pyrolysis process
17 assuming a 45-55 % carbon yield [36]. A characterization of the preform porosity was done in
18 our previous work [24]: the average pore diameter is $2.25 \pm 0.29 \text{ }\mu\text{m}$; the open and closed
19 porosities are estimated to be 42.3 ± 1.8 % and 0.7 ± 0.3 % respectively.

20

21 **2.2 Reactive melt infiltration assisted by microwave**

22 The setup employed in this research to heat by MW the preform is depicted in Fig. 1. The
23 external Al_2O_3 crucible was produced by tape casting, wrapping [37] and sintering [35] an
24 alumina tape (0.3 mm thickness) in order to obtain a very thin wall (~ 1 mm) cylinder. The
25 motivation was to have a container mostly transparent to MW. The vessel was then partially
26 filled (level 1 in Fig. 1) with a mixture of 75 wt% 10 μm grain size SiC (Ziegler, Winterthur,
27 Switzerland) and 25 wt% of 40 μm grain size BN powder (Henze Boron Nitride Products,
28 Lauben, Germany). On level 1 it was placed an inner container and wicks in Sigraflex™ (SGL
29 Carbon, Wiesbaden, Germany) filled with 50 g of silicon grains (HQ1, Sicerma, Erkelenz,
30 Germany) with a grit size of 0.2-2.0 mm.

31 The amount of silicon was calculated to infiltrate and convert the Sigraflex™ parts and the
32 preform into SiC whilst adding some extra amount. The preform was placed on the top of the

1 wicks. In some experiments a preform with a concentric hole was used in order to read directly
2 the temperature of molten silicon at the bottom.

3 The cylinder was then closed with a perforated lid of Sigraflex™ to separate the reactive part of
4 the setup from the SiC/BN powders. A BN tube was finally placed through the lid in
5 correspondence of a hole on the preform to create an access for the pyrometer (PYROSPOT
6 DSR10N, DIAS Infrared Systems GmbH, Schlattingen, Germany). Finally, the rest of SiC/BN
7 powder was placed inside the Al₂O₃ crucible in order to fill it; then the crucible was covered
8 with an Al₂O₃ capping. The infiltration set up was rotated in order to homogenize the
9 temperature during MW heating. The unique spot available for the pyrometer reading was then
10 the centre of rotation of the set up. The BN tube was carefully placed on this spot with a first
11 rotation test with the open furnace.

12 As described in detail in a previous paper [9], the scope of the of the SiC/BN powders was to
13 realise both a diffused MW susceptor and an insulation for thermal runaways.

14 The set-up was positioned on a rotating plate of porous alumina in the center of the microwave
15 furnace (Frick und Mallah Microwave Technology, Peine, Germany). Rotation (20 RPM) was
16 necessary to homogenise the MW field and avoid hot spots inside the multimode cavity. The
17 furnace chamber was connected to four circular waveguides carrying a TM₀₁ mode at 2.45
18 GHz. Each waveguide is supplied by an independent microwave generator delivering a power
19 of 2 kW. Further details on the furnace and its working parameters can be found in [9]. A 2-
20 colour pyrometer with an integrated digital camera was used to align the setup with the rotation
21 axis of the turning plate in order to have a reliable temperature reading. The pyrometer
22 measures the temperature in the range from 700 °C and 1800 °C; it was calibrated in our
23 laboratory with dedicated tests on silicon and graphite. The furnace was purged and then filled
24 with argon at 1.4 bar. Lower absolute pressures could not be achieved during MW processing
25 due the formation of Ar plasma. Fig. 2 shows the experimental profiles of the system
26 temperature [°C] vs time [min] obtained by varying the power lever. The maximum reached
27 temperature cannot be reported because of it exceeds the upper limit of the pyrometer. As
28 already reported in [9] the MW-RMI process is extremely fast: the power was kept ON till
29 reaching the complete melting of Silicon (end of the dwell); at the onset of a second
30 temperature peak the power was turned OFF. The temperature kept increasing, sustained by the
31 exothermic reaction between silicon and carbon inside a quasi-adiabatic vessel. Three power
32 levels were employed to heat up the chamber: they were corresponding to 30 %, 60 % and

1 75 % of the full power (8 kW). Higher power was avoided because of it would risk to affect the
2 process stability: at the start up the risk concerns an arcing plasma formation and, for long
3 experiments it is necessary avoid the waveguides' overheating.

4 5 **2.3 Characterization tests**

6 Three graphite-Si-SiC materials labelled P30, P60 and P75 were obtained by setting the power
7 level at 30 %, 60 % and 75 % of the full power respectively. The three samples had a disk
8 shape with a diameter of 50 mm and a thickness of around 6 mm. Their surfaces were initially
9 polished with SiC grinding paper (Grit from 180 to 800) in order to remove silicon residuals
10 after the infiltration process. The disks were cut in order to obtain samples with suitable size for
11 the different characterization tests. Three points bending tests were performed on a set of 8 bars
12 with size of 30x55x13 mm³ by using a universal tensile testing machine (Zwick Z050, Ulm,
13 Germany) with a span of 20 mm. A preloading of 5 N was used and the crosshead rate was 0.2
14 mm/min according to standard ASTM C1161-18. The samples were then subjected to a second
15 finer polishing step by using SiC grinding paper (Grit from 800 to 4000) followed by polishing
16 cloths loaded with lubricant and progressively smaller diamond abrasives (3 μm and 1 μm
17 respectively). The microstructure of the polished specimens and the fracture surfaces were
18 investigated by scanning electron microscopy (SEMFEG Assing SUPRA 25, equipped with
19 EDS Oxford INCA X-sight, Oberkochen, Germany). The micrographs have been obtained by
20 using backscattered electrons detector, which displays the atomic number contrast allowing to
21 better distinguish the different constituent phases.

22 Raman measurements were performed using a Raman microscope (InViaH, Renishaw, Wotton-
23 under-Edge, United Kingdom) equipped with a green laser source (wavelength: 514.5 nm).

24 Samples named P30 and P75 were placed on a microscope glass glide and the spectra acquired
25 in several points having different visual appearance (black, white or grey) were compared. For
26 each measured region we started with a low magnification objective (5x) zooming-in using a
27 20x and finally recording spectra with a 50x objective. The area of each examined spot was of
28 about 2 μm². Raman analysis being a volume technique, the signal is gathered from the sample
29 surface up to a depth that varies with the optical properties of the analysed materials. In sp²
30 rich carbon materials this depth is of a few micrometers [38]. The laser power was set at 5 mW
31 in order to obtain a good signal-to-noise ratio avoiding in the meantime damage of the sample

1 due to excessive heating. Each measurement was carried out in extended mode (100 cm^{-1} to
2 3500 cm^{-1}) with an exposure time of 10 s and with 3 accumulations.

3 The Raman analysis was mainly focused on three spectral regions in which the most relevant
4 features are:

5 1) peak centred at 520 cm^{-1} . This peak is typical of crystalline silicon [39].

6 2) peaks centred at 790 cm^{-1} . This peak is reported in literature [40] as arising from thin films
7 of 3C-SiC and it is associated to the transverse optical (TO) phonon modes.

8 3) peak close to 960 cm^{-1} . This peak can be due either to c-SiC and/or to the longitudinal optical
9 (LO) phonon modes of 3C-SiC.

10 4) two peaks close 1350 and 1590 cm^{-1} respectively. These are the D and G peaks of sp^2
11 coordinated carbon atoms [41].

12 The cross section for the various peaks is different and depends on the specific environment.

13 Therefore the analysis of the peaks intensities is not sufficient in order to determine the
14 percentage of the different phases when they coexist. However, by comparing the relative
15 intensities of the peak related to the various phases we can verify if the amount of one phase is
16 higher or lower in different samples [42]. To this purpose we proceed as follows:

17 1) the 520 cm^{-1} was selected as an indicator for Si abundance

18 2) the 790 cm^{-1} was selected as an indicator for SiC abundance. This peak was picked over 960
19 cm^{-1} as this last overlaps with a Si contribution

20 3) the G peak was selected as an indicator for graphite abundance. This peak was selected
21 instead of D peak as all sp^2 bonds contribute to its intensity while for the D peaks only those
22 sp^2 bonds close to the edge regions of grains contribute [43]

23 4) for each sample the area (i.e. the signal intensity integrated over the peak region) of each
24 relevant peaks is evaluated

25 5) the intensity ratios for SiC/Si and SiC/C peaks are evaluated

26 6) as an additional information about disorder in the graphite phase, the I_D/I_G (i.e. the ratio of
27 intensities of the D and G peaks) ratio is evaluated [43]

28 7) the FWHM (Full Width Half Maximum) of the Si and SiC related peaks is computed in
29 order to gather information on the local disorder [44] and the grain size in the Si and SiC
30 regions [45].

31 The crystalline phases of C-Si-SiC materials were identified by using X-ray diffraction

32 (Panalytical X'PERT PRO PW3040/60, Cu $K\alpha$ radiation at 40kV and 40mA, Panalytical BV,

1 Almelo, The Netherlands). The elaboration of XRD spectra for quantitative phase analysis was
2 performed by using MAUD program [46,47].

3 The thermal behavior was investigated by testing samples ($3\times3\times3$ mm³ in size) to a
4 temperature run from 25° to 1200 °C with a heating rate of 5°C/min under flowing air (50
5 ml/min) in a thermal analyzer [TGA/STDA851°, Mettler Toledo, Columbus, Switzerland].

7 **3. Results**

8 **3.1. Composite microstructure**

9 Fig. 3 shows the evolution of graphite-Si-SiC microstructure by varying the microwave power
10 level from 30 % (Fig. 3A) to 75 % (Fig. 3C). EDS analyses [performed] on areas with different
11 colour appearance [show] that the black parts are mainly constituted of carbon. [Specifically], the
12 lamellar structure identified for these areas allows us to assume the presence of unreacted
13 graphite. The brightest irregular spots, hereafter referred to as white areas, are mainly made of
14 unreacted silicon.

15 The grey regions are constituted by both silicon and carbon; EDS analyses on these areas show
16 an atomic ratio between the two elements close to 1:1 allowing us to speculate that the silicon
17 carbide formed by reactive infiltration.

18 All the microstructures present a similarity in the phases distribution: the carbon is always
19 isolated from the silicon by a SiC layer; [moreover the] silicon is surrounded by areas rich in SiC
20 produced during reactive infiltration. A similar microstructure has been previously reported in
21 the literature [48]. By observing a black carbon area in a larger magnification (Fig. 3D) SiC can
22 be found among the graphite layers. It can be supposed that silicon infiltrated the plates and
23 formed a thin SiC layer, which insulated the residual liquid silicon from carbon regions.

24 The fracture surfaces of P30, P60 and P75 samples (Fig. 4) were observed to be mainly flat
25 indicating a brittle fracture behaviour. Graphite flakes pull-out was observed in all the samples
26 and this phenomenon seems particularly evident in the material processed by using the highest
27 power level (Fig. 4C and 4D). [It] may be assumed that the observed pull-out can promote a
28 toughening of the ceramics.

29 In literature only few information is available about the microwaves effect on fibre/flakes pull-
30 out. Omatete et al. [49] observed a significant fiber pull-out from the analysis of fracture
31 surface of reaction bonded silicon nitride composites processed at 1250 °C for 8 h in a
32 microwave furnace. The samples nitrided at the higher temperature of 1350 °C exhibited only

1 limited pull-out probably due to the fibre degradation and a strong matrix-fibre bonding. This
2 study seems to confirm that temperature has a significant impact on the pull-out.

3 Moreover Papargyris et al. [50] reported that the fracture surface of composites produced with
4 conventional method exhibits a more extensive fibre pull-out compared to that produced using
5 microwaves. So the use of microwaves seems not to promote the pull-out effect. However any
6 study is present on the effect of MW power variation on the microstructure of RMI materials; a
7 more detailed investigation **has to be done**.

8 The presence of uniformly distributed pores of different sizes is particularly evident in sample
9 P30 compared to specimens obtained setting a higher power level.

11 **3.2 Raman characterization**

12 Samples obtained using the lowest (P30) and the highest power level (P75) were examined, and
13 the Raman spectra collected focusing on areas with different visual appearance (black, white or
14 grey) were compared. Both precursors, i.e. graphite starting powder and crystalline silicon,
15 were investigated in order to be used as references.

17 **3.2.1 Graphite and silicon precursor analysis**

18 The Raman spectra reported in Fig. 5A evidence a high quality graphitic material with a low
19 intensity D peak centered at 1350 cm^{-1} and an intense narrow G peak centered at 1572
20 cm^{-1} . These peaks are very well separated and the $I_D/I_G (= 0.16)$ ratio is typical of high quality
21 graphite [51]. This observation is supported by the following additional facts: 2D peak (around
22 2700 cm^{-1}) is strong and intense, left shouldered and typical of multi-layered graphite; D+G
23 Overtone peak ($\sim 2920\text{ cm}^{-1}$) is absent; and 2G peak at 3230 cm^{-1} is weak and sharp.

24 The crystalline silicon Raman Spectra reported in Fig. 5B shows, as expected, an intense and
25 very narrow peak centered at 520 cm^{-1} , and a broad band just below around 965 cm^{-1} [52].

27 **3.2.2 P30 Sample Raman Analysis**

28 Fig. 6 is an optical image showing the grey (Fig. 6A), the white (Fig. 6B) and the black (Fig.
29 6C) areas where the Raman spectra were measured.

30 Two different points were sampled both in the white and black zones of the material while
31 spectra from four different points were acquired in the grey zones. All Raman spectra displayed
32 in the figures have been background subtracted.

1 The Raman spectra of white areas are reported in Fig. 7A. These regions are rich in crystalline
2 silicon as shown by the intense peak $\sim 520\text{ cm}^{-1}$, slightly downshifted and quite enlarged if
3 compared with the crystalline precursor. The crystalline silicon structure is more disordered
4 than that of the c-Si (crystalline silicon) precursor due to the SiC production process. The
5 presence of an intense peak around 960 cm^{-1} as it is not accompanied by the 760 cm^{-1} peak
6 typical of SiC can be attributed to the crystalline c-Si Raman spectra. No clear evidence of the
7 presence of SiC in this region can be found. Other significant features are the presence of the
8 graphite-related peaks at 1350 cm^{-1} and 1580 cm^{-1} (D and G peaks) as well as of 2D, D+G and
9 2G peaks starting from 2960 cm^{-1} . This suggests the presence of unreacted graphite particles in
10 the white region.

11 The Raman spectra of the black areas are shown in Fig. 7B. This region appears to be rich in
12 carbon material with limited amounts of crystalline silicon and SiC indicated respectively by
13 519 and 789 cm^{-1} peaks. The carbon related peaks are the most intense and D and G peaks are
14 well separated. $I_D/I_G (= 0.88)$ is significantly higher than the value in the precursor graphite.
15 The graphitic structure is more defective compared with the original graphitic precursor. The
16 2D zone appears intense, left shouldered (index of multi-layered structure), and defective
17 (presence of D+G peak). The 2G peak has typical intensity and width.

18 The Raman spectra of the grey regions are displayed in Fig. 8A. In this region a relevant
19 amount of Si is present (sharp and intense 519 cm^{-1}) and the presence of graphitic carbon is
20 evident too (D and G peaks sharp and intense). The presence of SiC is confirmed by the peak at
21 793 cm^{-1} .

22 The non-negligible presence of both silicon and carbon in grey regions can be explained
23 considering a compositional inhomogeneity. This is evident from the SEM image of a grey area
24 (Fig. 8B) which shows the presence of both white and black contaminations within the grey
25 region.

26

27 **3.2.3 P75 sample Raman analysis**

28 Similarly to what was observed for sample P30, the microstructure of specimen P75 appears as
29 a structure of spotted black, white and grey zones (Fig. 6). For this reason, we acquired the
30 Raman spectra on these different areas to assess the compositional differences.

31 The measured Raman spectra were reported after the background subtraction.

1 The spectra of white region are reported in Fig. 9A. This zone is rich of pure c-Si confirmed by
2 the intense peak $\sim 519\text{ cm}^{-1}$, which is slightly downshifted and with a higher FWHM if
3 compared to crystalline silicon. The crystalline structure appears to be more disordered due to
4 the SiC production process, as previously observed in P30 sample. The presence of a weak but
5 detectable peak at 792 cm^{-1} is due to the TO mode of SiC. This indicates the presence of a low
6 amount of SiC. Other significant features (related to graphite) are the presence of D and G
7 peaks at 1350 cm^{-1} and 1580 cm^{-1} respectively and evidence of 2D, D+G and 2G peaks starting
8 from 2960 cm^{-1} . Hence, in this region disordered c-Si is dominant, but a small amount of
9 unreacted graphite is present as well as SiC traces.

10 The Raman spectra of black region is reported in Fig. 9B. This area appears to be rich of
11 graphitic material with limited Si and SiC presence, evidenced by the peaks at 518 cm^{-1} (Si)
12 and 792 cm^{-1} (SiC). The graphite related peaks are by far the most intense. D and G peaks are
13 quite narrow. $I_D/I_G (= 0.45)$ is low but significantly higher than the value of the precursor
14 graphite. The graphitic structure is more defective than in the original graphitic precursor. This
15 conclusion is supported by an intense, left shouldered 2D zone (index of multi-layered
16 structure), and the presence of D+G peak (indicating a more defective structure).

17 The Raman spectra of grey regions is shown in Fig. 9C. In this zone Si related peaks are absent
18 while weak carbon related peaks can be observed: D and G peaks (this last is rather broadened),
19 2D peak is weak and D+G peak can be barely seen. The peaks centred at 794 cm^{-1} and 970 cm^{-1}
20 indicates the presence of thin film of 3C-SiC deposited with different C/Si ratio. All spectra
21 collected in the different grey points show sharp optical transverse peak (TO) and longitudinal
22 optical (LO) SiC peak, respectively around 794 cm^{-1} and 970 cm^{-1} [53]. No peaks related to c-
23 Si can be observed, indicating that the c-Si has fully converted to SiC (in the limit of detection
24 of the Raman technique).

25 However, the ratio of the intensities of SiC peak at 794 cm^{-1} to carbon G peak is much higher
26 compared to that of sample P30. Moreover, the I_D/I_G ratio is lower for sample P75 compared to
27 P30 (0.29 and 0.98 respectively) indicating a higher level of disorder of the carbon-rich region
28 of the latter.

29 In order to support the meaningfulness of the approach used in this paper, a Raman mapping of
30 sample P75 has been performed (Fig. 10). Fig. 10A shows the mapped region ($50\mu\text{m} \times 70\mu\text{m}$)
31 obtained using the optical microscope. This area is divided into several points; the spectra are
32 acquired sequentially from this range of points, across the specified area of interest. Figure 10B

1 shows the mapping of the intensity of the SiC peak (brighter areas indicates higher intensity),
2 while Fig. 10C and Fig. 10D show the mapping of the intensity of the Si and graphite
3 characteristic Raman peaks respectively.

4 By comparing the obtained maps with the optical image it is evident that the regions which
5 appears bright in the optical image correspond to Si-rich regions, while the dark regions mainly
6 correspond to C-rich areas. This Raman approach is able to easily highlight the regions where
7 the sample is richer in SiC component. Most SiC-rich regions are present in the boundary
8 regions between Si-rich and C-rich zones while others are clearly present where Si and C
9 signals are lower.

11 3.3 X-ray diffraction

12 Fig. 11 shows the XRD spectra for graphite-Si-SiC materials obtained by varying the power
13 level during the RMI process.

14 The most intense peaks belong to β -SiC phase, which is considered the stable form of SiC up to
15 2100 °C [54]. The other more common SiC polytypes such as 4H, 6H and 15R were not
16 detected.

17 The chemical reaction between carbon and silicon leading to the formation of SiC was not
18 complete as evidenced by the presence in XRD spectra of additional peaks assigned to both
19 unreacted graphite and silicon.

20 The chemical composition of the starting preform (Table 1) evidences the presence of a low but
21 not negligible amount of glassy carbon, which is a non-graphite form of carbon having a
22 microstructural disorder between that of amorphous carbon and single-crystal graphite [55].

23 The XRD spectrum of glassy carbon usually shows broad peaks at 2theta values typical of
24 graphite peaks [56]. No broad peaks are present in XRD spectra of C-Si-SiC materials (Fig.
25 11). This can be explained considering that the high temperature reached during the infiltration
26 process should allow the development from a glassy carbon structure into a graphite-like layer
27 structure. This implies an increment of crystal structure order highlighted by the narrowing of
28 the diffraction peaks [56,57].

29 The relative amount of formed SiC was calculated to be 49.3 wt%, 54.9 wt% and 75.7 wt% for
30 P30, P60 and P75 samples respectively. The conversion of graphite based preform and silicon
31 into SiC is observed to be higher by using a higher power level.

32

3.4 Mechanical and thermal properties

Preliminary results of mechanical and thermal properties are reported in order to understand how the microstructure of graphite-Si-SiC can influence the material properties.

The bending strength values increase by increasing the microwave power level: the average value of 146 ± 24 MPa for P30 is lower with respect to 160 ± 16 MPa and 177 ± 11 MPa values obtained for P60 and P75 respectively. These values are comparable to those reported for commercially available SUPERSiC® material (bending strength ~ 147 MPa) produced converting starting graphite based preforms to high purity silicon carbide using a reactive SiO flow [58]. However the experimental strength values result lower respect to those observed for fully infiltrated Si-SiC material [9,59].

In Fig. 12 the bending tests curves for P75 samples (reported as example) show two different behaviours. It is interesting to note that some specimens show a linear stress-strain relationship typical of brittle materials. On the other hand, samples obtained from a different part of the starting disk, report a quite higher displacement before rupture. As shown in the upper part of Fig. 12 the samples were obtained by making a series of cuts in a perpendicular direction respect to the base of the starting disk. Some of these bars showed a thin crack filled with solid silicon. This is a common defect in materials processed by RMI process. Previous studies attributed this phenomenon mainly to CTE mismatch between the formed SiC and the unreacted graphite [48,60]. The different trends in bending strength curves can be correlated to the different microstructure between samples which evidences the presence of Si-filled cracks with respect to those in which the crack is absent. The material showing a standard brittle behavior displays a homogeneous microstructure similar to those presented in Fig. 3. On the other hand, the microstructure of specimens showing the crack displays an intermediate plateau before reaching the material fracture. However, the bending strength values of the two set of samples is very similar so the presence of silicon-filled cracks seems not affecting the strength of graphite-Si-SiC materials. Similar considerations can be done for samples P30 and P60. The mechanical performance of Si-SiC materials depends on the volume fraction of silicon carbide: the higher is the amount of formed SiC, the stronger is the interconnectivity of SiC boundaries, which allow to obtain enhanced strength.

The analysis of bending strength curves cannot evidence the toughening effect supposed by observing the graphite pull out from the fracture surfaces. This conclusions has in fact to be confirmed by a more detailed study of the mechanical behavior of these materials.

1 Thermogravimetric analyses of graphite-Si-SiC material from room temperature up to 1200 °C
2 in flowing air have been performed in order to investigate the thermal stability. Fig. 13 shows
3 the TGA curve for sample P75, which was taken as example because it resulted the best
4 infiltrated and densest material.
5 No change in weight was observed up to a temperature of 720 °C. For higher temperature the
6 material starts to decrease its weight becoming stable again at a weight of about 79 % of the
7 starting value. The one step weight decrease is probably due to the decomposition of the
8 unreacted graphite in an oxidizing environment.

9

10 **4. Discussion**

11 Graphite-Si-SiC ceramics were obtained by reactive infiltration of liquid silicon into graphite-
12 based preforms. Starting from large blocks graphite was ground to obtain micrometer size
13 particles; this introduced defects and enlarges its reacting surface area. Ground graphite is in
14 fact far from its theoretical lattice stacking; many defects are present such as decreasing
15 crystalline order, dangling bonds, irregular bond angles and angstrom-scale porosity [61].
16 These defects are directly related to the concentration and the accessibility of “active sites”,
17 which enhance the chemical reactivity of carbon making the infiltration process difficult.
18 The process was assisted by microwaves, which provide a fast heating of the starting materials
19 allowing to reduce both the consumption of energy and the processing time with respect to
20 conventional heating. Three sets of samples were prepared by varying the microwave power:
21 P30, P60 and P75 specimens were in fact produced by using a power of 30 %, 60 % and 75 %
22 of the full power respectively.

23 The investigation of microstructure shows the presence of three main interpenetrated phases:
24 black areas coming from unreacted graphitic preforms, white silicon islands and residual grey
25 silicon carbide. The presence of both unreacted silicon and graphite put in evidence that the
26 reaction between these two phases is not complete leaving residual starting materials in the
27 final material microstructure. However, the grey SiC areas result the most interesting ones
28 because of its relative amount and distribution influence the final material properties. SiC is
29 formed at the interface between silicon and graphite and progressively grows producing a
30 silicon carbide network. X-ray diffraction spectra confirm that silicon, carbon and SiC are the
31 three main crystalline phases present in all the samples of graphite-Si-SiC, independently from
32 the used microwave power.

1 SiC shows a cubic structure whose formation is expected because of the conversion into
2 hexagonal form generally occurs at temperature higher than 2100 °C [54,62]. During the RMI
3 process the temperature increases beyond the upper limit of the pyrometer sensor (1800 °C), so
4 it is not possible to measure the maximum reached temperature. However Cornolti et al. [24]
5 studied the RMI process in detail elaborating a model which is demonstrated to be in good
6 agreement with the experimental temperature history. According to this model the maximum
7 temperature was estimated to be around 2000°C.

8 The formation of β -SiC with a cubic structure is however very common in materials obtained
9 by RMI [59,63]. Margiotta et al. [24] investigated the liquid silicon infiltration of carbon
10 preforms derived from carbonization of crystalline cellulose and phenolic resin blends. The
11 process performed between 1414 °C and 1900 °C evidenced the formation of β -SiC in addition
12 to residual Si at all temperatures.

13 However, it is necessary to consider that the transition from β to α forms could be affected by
14 the other processing conditions (such as pressure, the use of microwave etc) in addition to the
15 temperature. Therefore, it cannot be excluded the formation of a small amount of SiC with a
16 hexagonal crystal structure. The XRD spectra did not put in evidence the formation of this SiC
17 polytype because of they could be present in an amount smaller than the detection limit of XRD
18 technique.

19 The intensity of SiC peaks increases from P30 to P75: the amount of this phase is therefore
20 higher for sample P75. The formation of SiC is therefore favored by increasing the supplied
21 MW power. This confirms the higher efficiency of the RMI process in the P75 case previously
22 deduced from XRD measurements. Raman analyses also confirm this results; in fact in sample
23 P75 the presence of SiC associated peaks is more evident than in P30, suggesting a higher
24 efficiency of the process in the P75 case.

25 Moreover, Table 2 was prepared in order to compare and discuss the results coming from the
26 Raman spectra. The main parameters which characterize a Raman peak, the center and the
27 width respectively, were reported and compared for the starting materials (silicon and graphite)
28 and the samples produced by setting the lowest and highest MW power (P30 and P75 samples
29 were subdivided in their components: white, black and grey). For each sample the contribution
30 due to Si, SiC, and carbon (D and G peaks) components was moreover considered. Last three
31 columns report the ratio of peak areas (Si, SiC, and carbon characteristics peaks D and G).

1 These ratios show the contribution in the different regions (white, black, grey) of the various
2 components (Si, SiC and carbon material).
3 In particular, SiC/G and SiC/Si ratios can be used to evaluate the presence of SiC in the region
4 under study: in fact high values of these ratios imply that an increased amount of SiC is formed.
5 Consequently the relative amount of both Si and carbon starting material progressively
6 decreases. Both SiC/G and SiC/Si ratios are significantly higher in P75 grey region if compared
7 to P30.
8 The influence of microwave power on the mechanical and thermal properties of graphite-Si-
9 SiC materials was preliminarily investigated.
10 The bending strength for samples increases in function of the higher used power. So it is
11 possible to hypothesize that applying a high power the formation of vapor silicon is favored
12 allowing the formation of an increased amount of SiC as confirmed by Raman and XRD. A
13 visual analysis of microstructural images (Fig. 3) reveals that SiC seems to form a more
14 continuous network for sample P75 with respect to P60 and P30. This may justify the
15 enhancement of P75 bending strength compared to the other samples. Moreover, a higher
16 porosity of sample P30 with respect to P75 is clear from the comparison of SEM micrographs
17 (Fig. 3). It is well known that the presence of pores significantly affects the material
18 mechanical properties resulting in lower bending strength.

20 5. Conclusions

21 Graphite-Si-SiC ceramic materials were successfully prepared by Reactive Melt Infiltration
22 process assisted by microwave. The effects of microwave power variation on the
23 microstructure and the mechanical properties of ceramics obtained by this process were
24 investigated.
25 The microstructure consists of a homogeneous distribution of interpenetrated phases. Residual
26 graphitic areas are separated from unreacted silicon islands by a SiC network. The reaction
27 between Si and graphite occurs at their interface and involves the formation of a growing SiC
28 layer. However, the reaction is not complete, leaving residuals of unreacted starting
29 components.
30 Raman and X-ray diffraction investigations show the strong correlation between the conversion
31 of graphite into SiC and the microwave power used. The relative amount of formed SiC
32 increases from 49.3 wt% to 75.7 wt% by increasing the power level from 30 % to 75 % of its

1 maximum value. The increment of the relative amount of formed SiC suggests a higher
2 efficiency of the infiltration process. Furthermore, the measurements of bending strength
3 confirm it show higher values for samples processed by using the highest power level. The
4 formation of a higher amount of SiC for sample P75 could explain the formation of a more
5 continuous SiC network. The improved mechanical behavior is hence linked to a more dense
6 material obtained by increasing the microwave power.

7

8 **Acknowledgements**

9 This research did not receive any specific grant from funding agencies in the public,
10 commercial, or not-for-profit sectors.

11 Authors wish to thank Prof. G. Annino from CNR, Pisa, Italy for providing data on dielectric
12 properties of SiC.

1 **References**

- 2
- 3 [1] E.O. Einset, Analysis of reactive melt infiltration in the processing of ceramics and
4 ceramic composites, *Chem. Eng. Sci.* 53 (1998) 1027–1039. doi:10.1016/S0009-
5 2509(97)00379-5.
- 6 [2] K. Morsi, Review: Reaction synthesis processing of Ni-Al intermetallic materials, *Mater.*
7 *Sci. Eng. A.* 299 (2001) 1–15. doi:10.1016/S0921-5093(00)01407-6.
- 8 [3] G. Rajesh, R.B. Bhagat, Infiltration of liquid metals in porous compacts: Modeling of
9 permeabilities during reactive melt infiltration, *Transp. Porous Media.* 36 (1999) 43–68.
10 doi:10.1023/A:1006574912165.
- 11 [4] D. Manfredi, M. Pavese, S. Biamino, P. Fino, C. Badini, NiAl(Si)/Al₂O₃ co-continuous
12 composites by double reactive metal penetration into silica preforms, *Intermetallics.* 16
13 (2008) 580–583. doi:10.1016/j.intermet.2008.01.010.
- 14 [5] E. Nelson, P. Colella, Parametric Study of Reactive Melt Infiltration, in: 1999 Int. Mech.
15 Eng. Congr. Expo., Nashville, Tennessee, 2000.
- 16 [6] J.C. Margiotta, D. Zhang, D.C. Nagle, C.E. Feeser, Formation of dense silicon carbide
17 by liquid silicon infiltration of carbon with engineered structure, *J. Mater. Res.* 23 (2008)
18 1237–1248. doi:10.1557/JMR.2008.0167.
- 19 [7] D. Wang, Y. Zeng, X. Xiong, G. Li, Z. Chen, W. Sun, Y. Wang, Preparation and
20 ablation properties of ZrB₂ – SiC protective laminae for carbon / carbon composites,
21 *Ceram. Int.* 40 (2014) 14215–14222. doi:10.1016/j.ceramint.2014.06.010.
- 22 [8] X. Yang, L. Wei, W. Song, Z. Bi-feng, C. Zhao-hui, ZrB₂ / SiC as a protective coating
23 for C / SiC composites : Effect of high temperature oxidation on mechanical properties
24 and anti-ablation property, *Compos. Part B.* 45 (2013) 1391–1396.
25 doi:10.1016/j.compositesb.2012.07.007.
- 26 [9] G. Bianchi, P. Vavassori, B. Vila, G. Annino, M. Nagliati, M. Mallah, S. Gianella, M.
27 Valle, M. Orlandi, A. Ortona, Reactive silicon infiltration of carbon bonded preforms
28 embedded in powder field modifiers heated by microwaves, *Ceram. Int.* 41 (2015)
29 12439–12446. doi:10.1016/j.ceramint.2015.06.087.
- 30 [10] U.F. Vogt, L. Gyo, A. Herzog, T. Graule, G. Plesch, Macroporous silicon carbide foams
31 for porous burner applications and catalyst supports, 68 (2007) 1234–1238.
32 doi:10.1016/j.jpccs.2006.12.008.

- 1 [11] A. Ortona, D. Trimis, V. Uhlig, R. Eder, S. Gianella, P. Fino, G. D'Amico, E. Boulet, C.
2 Chazelas, T. Gramer, E. Cresci, J.G. Wunning, H. Altena, F. Beneke, M. Debier, SiSiC
3 heat exchangers for recuperative gas burners with highly structured surface elements,
4 *Int. J. Appl. Ceram. Technol.* 11 (2014) 927–937. doi:10.1111/ijac.12087.
- 5 [12] W. Krenkel, F. Berndt, C/C-SiC composites for space applications and advanced friction
6 systems, *Mater. Sci. Eng. A* 412 (2005) 177–181. doi:10.1016/j.msea.2005.08.204.
- 7 [13] P. González, J. Serra, S. Liste, S. Chiussi, B. León, M. Pérez-Amor, J. Martínez-
8 Fernández, A.R. De Arellano-López, F.M. Varela-Feria, New biomorphic SiC ceramics
9 coated with bioactive glass for biomedical applications, *Biomaterials*. 24 (2003) 4827–
10 4832. doi:10.1016/S0142-9612(03)00405-8.
- 11 [14] L.W. Hilling WB, Mehan RL, Morelock CR, Decarlo VJ, Silicon-silicon carbide
12 composites, *Am. Ceram. Soc. Bull.* 54 (1975) 1054–1056. ISSN 0002-7812.
- 13 [15] D.M. Liu, B.W. Lin, Thermal conductivity in hot-pressed silicon carbide, *Ceram. Int.* 22
14 (1996) 407–414. doi:10.1016/0272-8842(95)00125-5.
- 15 [16] W.S. Yang, S. Biamino, E. Padovano, M. Pavese, S. Marchisio, G. D'Amico, S. Ceresa
16 Mio, X. Chen, P. Fino, C. Badini, Thermophysical properties of SiC multilayer prepared
17 by tape casting and pressureless sintering, *Compos. Struct.* 96 (2013) 469–475.
18 doi:10.1016/j.compstruct.2012.09.018.
- 19 [17] M.W. Chase, NIST-JANAF Thermochemical Tables, 4 Edition, American Chemical
20 Society, Woodbury, New York, 1998.
- 21 [18] Y.X. Wang, S.H. Tan, D.L. Jiang, The fabrication of reaction-formed silicon carbide
22 with controlled microstructure by infiltrating a pure carbon preform with molten Si,
23 *Ceram. Int.* 30 (2004) 435–439. doi:10.1016/S0272-8842(03)00128-7.
- 24 [19] R.N. Singk, Kinetics model for the growth of silicon carbide by the reaction of liquid
25 silicon with carbon, *J. Am. Ceram. Soc.* 78 (1995) 2456–62. doi:doi.org/10.1111/j.1151-
26 2916.1995.tb08685.x.
- 27 [20] C.E. Byrne, D.C. Nagle, Carbonization of Wood for Advanced Materials Applications,
28 *Carbon N. Y.* 35 (1991) 259–266. doi:10.1016/S0008-6223(96)00136-4.
- 29 [21] C.E. Byrne, D.C. Nagle, Cellulose derived composites - A new method for materials
30 processing, *Mater. Res. Innov.* 1 (1997) 137–144. doi:10.1007/s100190050031.
- 31 [22] J.F. White, L. Ma, K. Forwald, D. Sichen, Reactions between silicon and graphite
32 substrates at high temperature: In situ observations, *Metall. Mater. Trans. B Process*

- 1 Metall. Mater. Process. Sci. 45 (2014) 150–160. doi:10.1007/s11663-013-9947-0.
- 2 [23] R. Israel, R. Voytovych, P. Protsenko, B. Drevet, D. Camel, N. Eustathopoulos,
3 Capillary interactions between molten silicon and porous graphite, *J. Mater. Sci.* 45
4 (2010) 2210–2217. doi:10.1007/s10853-009-3889-6.
- 5 [24] L. Cornolti, S. Martinelli, G. Bianchi, A. Ortona, Microwave heating controlled reactive
6 melt infiltration for Graphite-Si-SiC ceramics manufacturing, *J. Am. Ceram. Soc.* 00
7 (2018) 1–12. doi:doi.org/10.1111/jace.16124.
- 8 [25] P.G. Karandikar, M.K. Aghajanian, D. Agrawal, J. Cheng, Microwave Assisted (Mass)
9 Processing of Metal-Ceramic and Reaction-Bonded Composites, *Mech. Prop. Perform.*
10 *Eng. Ceram. II Ceram. Eng. Sci. Proc.* 27 (2008) 435–446.
11 doi:10.1002/9780470291313.ch42.
- 12 [26] G. Danko, R. Silbergliitt, P. Colombo, E. Pippel, J. Woltersdorf, Comparison of
13 Microwave Hybrid and Conventional Heating of Preceramic Polymers to Form Silicon
14 Carbide and Silicon Oxycarbide Ceramics, *J. Am. Ceram. Soc.* 25 (2000) 1617–1625.
15 doi:10.1111/j.1151-2916.2000.tb01440.x.
- 16 [27] E. Breval, J.P. Cheng, D.K. Agrawal, P. Gigl, M. Dennis, R. Roy, A.J. Papworth,
17 Comparison between microwave and conventional sintering of WC/Co composites,
18 *Mater. Sci. Eng. A.* 391 (2005) 285–295. doi:10.1016/j.msea.2004.08.085.
- 19 [28] B. Garcia-Baños, J.M. Catalá-Civera, F.L. Peñaranda-Foix, P. Plaza-González, G.
20 Llorens-Vallés, In situ monitoring of microwave processing of materials at high
21 temperatures through dielectric properties measurement, *Materials (Basel).* 9 (2016).
22 doi:10.3390/ma9050349.
- 23 [29] A. Kumar, S. Sharma, Loss Factor of the Dielectric Material At Microwave Frequencies,
24 *Prog. Electromagn. Res.* 69 (2007) 47–54. doi:10.2528/PIER06111204.
- 25 [30] M. Hotta, M. Hayashi, M.T. Lanagan, D.K. Agrawal, K. Nagata, Complex Permittivity
26 of Graphite, Carbon Black and Coal Powders in the Ranges of X-band Frequencies (8.2
27 to 12.4 GHz) and between 1 and 10 GHz, *ISIJ Int.* 51 (2011) 1766–1772.
28 doi:10.2355/isijinternational.51.1766.
- 29 [31] J. Krupka, S. Member, J. Breeze, A. Centeno, N. Alford, T. Claussen, Measurements of
30 Permittivity , Dielectric Loss Tangent , and Resistivity of Float-Zone Silicon at
31 Microwave Frequencies, *IEEE Trans. Microw. Theory Tech.* 54 (2006) 3995–4001.
- 32 [32] T. Baeraky, Microwave measurements of the dielectric properties of silicon carbide at

- 1 high temperature, Egypt. J. Sol. 25 (2002) 263–273. doi:10.1016/B978-1-59749-266-
2 9.00017-5.
- 3 [33] J.A. Menéndez, A. Arenillas, B. Fidalgo, Y. Fernández, L. Zubizarreta, E.G. Calvo, J.M.
4 Bermúdez, Microwave heating processes involving carbon materials, Fuel Process.
5 Technol. 91 (2010) 1–8. doi:10.1016/j.fuproc.2009.08.021.
- 6 [34] G. Annino, personal communication, HELM, "High-frequency Electro-magnetic
7 technologies for advanced processing of ceramic matrix composites and graphite
8 expansion, n.d. <http://www.helm-project.eu>.
- 9 [35] D. Jakobsen, H. Rauch, S. Dudczig, D. Schumacher, A. Roosen, Conceptual design and
10 manufacture of spirally wound alumina tubes with improved thermal shock behavior for
11 refractory applications, J. Mater. Process. Technol. 229 (2016) 623–632.
12 doi:10.1016/j.jmatprotec.2015.10.024.
- 13 [36] A. Ortona, P. Fino, C.D. Angelo, S. Biamino, G.D. Amico, D. Gaia, S. Gianella, Si-SiC-
14 ZrB₂ ceramics by silicon reactive infiltration, 38 (2012) 3243–3250.
15 doi:10.1016/j.ceramint.2011.12.030.
- 16 [37] M. Pavese, P. Fino, A. Ortona, C. Badini, Potential of SiC multilayer ceramics for high
17 temperature applications in oxidising environment, Ceram. Int. 34 (2008) 197–203.
18 doi:10.1016/j.ceramint.2006.09.008.
- 19 [38] N. Zhenhua, Y. Wang, Y. Yu, S. Zexiang, Raman Spectroscopy and Imaging of
20 Graphene, Nano Res. 1 (2008) 273–291. doi:10.1007/s12274-008-8036-1.
- 21 [39] J.H. Parker Jr., D.W. Feldman, M. Ashkin, Raman scattering by silicon and germanium,
22 Phys. Rev. 155 (1967) 712. doi:10.1103/PhysRev.155.712.
- 23 [40] D.W. Feldman, J.H. Parker, W.J. Choyke, L. Patrick, Phonon dispersion curves by
24 raman scattering in SiC, polytypes 3C, 4H, 6H, 15R, and 21R, Phys. Rev. 173 (1968)
25 787–793. doi:10.1103/PhysRev.173.787.
- 26 [41] A.C. Ferrari, J. Robertson, Interpretation of Raman spectra of disordered and amorphous
27 carbon, Phys. Rev. B. 61 (2000) 14095–14107. doi:10.1103/PhysRevB.61.14095.
- 28 [42] M.R. Joya, K.M. Fonseca, J. Barba-Ortega, Difference in the relative intensities Raman
29 of the perovskite PLT with temperature, in: AIP Conf. Proc. Electroceramics XIV Conf.,
30 American Institute of Physics, 2014: pp. 42–45. doi:10.1063/1.4901655.
- 31 [43] A.C. Ferrari, D.M. Basko, Raman spectroscopy as a versatile tool for studying the
32 properties of graphene, Nat. Nanotechnol. 8 (2013) 235–260.

- 1 [44] D. Beeman, R. Tsu, M.F. Thorpe, Structural information from the Raman spectrum of
2 amorphous silicon, *Phys. Rev. B.* 32 (1985) 874–878.
3 doi:<https://doi.org/10.1103/PhysRevB.32.874>.
- 4 [45] A.K. Arora, M. Rajalakshmi, T.R. Ravindran, V. Sivasubramanian, Raman spectroscopy
5 of optical phonon confinement in nanostructured materials, *J. Raman Spectrosc.* 38
6 (2007) 604–617. doi:10.1002/jrs.1684.
- 7 [46] L. Lutterotti, Maud: a Rietveld analysis program designed for the internet and
8 experiment integration, 2000.
- 9 [47] D. Chateigner, *Combined analysis*, first ed., John Wiley & Sons., Hoboken, NJ, USA,
10 2013.
- 11 [48] J.C. Margiotta, D. Zhang, D.C. Nagle, Microstructural evolution during silicon carbide
12 (SiC) formation by liquid silicon infiltration using optical microscopy, *Int. J. Refract.*
13 *Met. Hard Mater.* 28 (2010) 191–197. doi:10.1016/j.ijrmhm.2009.09.002.
- 14 [49] O.O. Omatete, T.N. Tiegs, A.C. Young, Gelcast reaction bonded silicon nitride
15 composites, in: *Proc. 15th Annu. Conf. Compos. Adv. Ceram. Mater. Ceram. Eng. Sci.*
16 *Proceedings*, Vol. 12, John Wiley & Sons, Inc., Hoboken, NJ, USA, 1991: pp. 1257–
17 1264. doi:<https://doi.org/10.1002/9780470313831.ch26>.
- 18 [50] D.A. Papargyris, R.J. Day, A. Nesbitt, D. Bakavos, Comparison of the mechanical and
19 physical properties of a carbon fibre epoxy composite manufactured by resin transfer
20 moulding using conventional and microwave heating, *Compos. Sci. Technol.* (2008).
21 doi:10.1016/j.compscitech.2008.01.010.
- 22 [51] S. Reich, C. Thomsen, Raman spectroscopy of graphite, *Philos. Trans. R. Soc. A Math.*
23 *Phys. Eng. Sci.* 362 (2004) 2271–2288. doi:10.1098/rsta.2004.1454.
- 24 [52] E.M. Kunimitsu Uchinokura, Tomoyuki Sekine, Raman scattering by silicon, *Solid State*
25 *Commun.* 11 (1972) 47–49. doi:[doi.org/10.1016/0038-1098\(72\)91127-1](https://doi.org/10.1016/0038-1098(72)91127-1).
- 26 [53] E.S. B Shi, XC Liu, MX Zhu, JH Yang, Effect of propane/silane ratio on the growth of
27 3C-SiC thin films on Si (100) substrates by APCVD, *Appl. Surf. Sci.* 259 (2012) 685–
28 690.
- 29 [54] Y. Wang, S. Tan, D. Jiang, The effect of porous carbon preform and the infiltration
30 process on the properties of reaction-formed SiC, 42 (2004) 1833–1839.
31 doi:10.1016/j.carbon.2004.03.018.
- 32 [55] P.K. Chu, L. Liuhe, Characterization of amorphous and nanocrystalline carbon films,

- 1 Mater. Chem. Phys. 96 (2006) 253–277. doi:10.1016/j.matchemphys.2005.07.048.
- 2 [56] S.S. Bukalov, L. Leites, I. Sorokin, S. Kotosonov, Structural Changes in Industrial
3 Glassy Carbon As a Function of Heat Treatment Temperature According To Raman
4 Spectroscopy and X-Ray, *Nanosyst. Physics, Chem. Math.* 5 (2014) 186–191.
- 5 [57] A.F. Craievich, On the structure of glassy carbon, *Mater. Res. Bull.* 11 (1976) 1249–
6 1255. doi:10.1016/0025-5408(76)90029-5.
- 7 [58] Poco Graphite, POCO SUPERSiC Materials,
8 <http://poco.com/Portals/0/Literature/Semiconductor/78956v3SUPERSiC Materials.pdf>.
- 9 [59] N.R. Calderon, M. Martínez-Escandell, J. Narciso, F. Rodríguez-Reinoso, The combined
10 effect of porosity and reactivity of the carbon preforms on the properties of SiC
11 produced by reactive infiltration with liquid Si, *Carbon N. Y.* 47 (2009) 2200–2210.
12 doi:10.1016/j.carbon.2009.04.002.
- 13 [60] R.S. Evans, D.L. Bourell, J.J. Beaman, M.I. Campbell, Reaction Bonded Silicon
14 Carbide: Sff, Process Refinement and Applications, *Solid Free. Fabr.* (2003) 414–422.
- 15 [61] P. Morgan, *Carbon fibers and their composites*, 1st ed., CRC Press, Boca Raton, 2005.
- 16 [62] S. Sugiyama, M. Togaya, Phase Relationship between 3C- and 6H-Silicon Carbide at
17 High Pressure and High Temperature, *J. Am. Ceram. Soc.* 16 (2001) 3013–3016.
18 doi:10.1111/j.1151-2916.2001.tb01129.x.
- 19 [63] J.M. Qian, Z.H. Jin, X.W. Wang, Porous SiC ceramics fabricated by reactive infiltration
20 of gaseous silicon into charcoal, *Ceram. Int.* 30 (2004) 947–951.
21 doi:10.1016/j.ceramint.2003.11.001.
- 22
23

1 **Tables**

2 **Table 1.** Change in composition of preform due to pyrolysis.

	Graphite [wt%]	Phenolic resin [wt%]	Glassy carbon [wt%]
Before pyrolysis	88.50	11.50	0
After pyrolysis	94.25	0	5.75

3
4
5
6

7 **Table 2.** Raman spectra parameters for peaks under study and their ratio. All values are in cm^{-1} .

	Si		SiC		D		G		Peak Ratio			
	(520 cm^{-1})		(790 cm^{-1})		(1350 cm^{-1})		(1590 cm^{-1})		SiC/Si	SiC/G	D/G	
	Center	Width	Center	Width	Center	Width	Center	Width				
Si	520	2	0	0	0	0	0	0	0	----	----	
Graphite	0	0	0	0	1349	23	1575	8	----	0	0.17	
P30	White	520	13	0	0	1346	16	1578	10	0.00	0.00	1.04
	Black	519	10	789	7	1349	22	1578	16	0.39	0.13	0.88
P75	Grey	519	11	793	5	1346	20	1578	17	0.01	0.02	0.98
	White	519	14	792	21	1340	40	1576	32	0.10	0.20	0.36
	Black	518	13	792	6	1348	20	1578	9	0.45	0.05	0.62
	Grey	520	13	794	5	1345	28	1577	51	4.44	1.81	0.29

8
9
10